

Listing of Claims

The following listing of claims will replace all prior versions, and listings, of claims in the subject application:

Claims 1-6 (canceled)

7. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising zinc oxide in a molar ratio with the basic material of 3% to 50% zinc oxide.

8. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising titanium oxide in a molar ratio with the basic material of 10% to 98% titanium oxide.

9. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising magnesium

oxide in a molar ratio with the basic material of 3% to 45% magnesium oxide.

10. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising yttrium oxide in a molar ratio with the basic material of 10% to 80% yttrium oxide.

11. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising gallium nitride in a molar ratio with the basic material of 1% to 30% gallium nitride.

12. (currently amended) A protection layer for a data recording medium, the protection layer comprising:

SiO<sub>2</sub> as a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising silicon nitride in a molar ratio with the basic material of 10% to 85% silicon nitride.

13. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising aluminum nitride in a molar ratio with the basic material of 1% to 50% aluminum nitride.

14. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising a silicon carbide in a molar ratio with the basic material of 5% to 50% silicon carbide.

15. (withdrawn) A protection layer for a data recording medium, the protection layer comprising:

a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising a titanium carbide in a molar ratio with the basic material of 10% to 85% titanium carbide.

16. (currently amended) A protection layer for a data recording medium, the protection layer comprising:

SiO<sub>2</sub> as a basic material; and

a compound having a thermal conductivity greater than or equal to 10 W/m.deg when in a bulk state, said compound comprising one or more of the compounds selected from the group consisting of:

zinc oxide in a molar ratio with the basic material of 3% to 50% zinc oxide,

titanium oxide in a molar ratio with the basic material of 10% to 98% titanium oxide,

magnesium oxide in a molar ratio with the basic material of 3% to 45% magnesium oxide,

yttrium oxide in a molar ratio with the basic material of 10% to 80% yttrium oxide,

gallium nitride in a molar ratio with the basic material of 1% to 30% gallium nitride,

silicon nitride in a molar ratio with the basic material of 10% to 85% silicon nitride,

aluminum nitride in a molar ratio with the basic material of 1% to 50% aluminum nitride,

silicon carbide in a molar ratio with the basic material of 5% to 50% silicon carbide, and

titanium carbide in a molar ratio with the basic material of 10% to 85% titanium carbide.

17. (new) A protection layer as claimed in claim 12, wherein the compound includes a combination of the silicon nitride and zinc oxide, aluminum oxide, titanium oxide, magnesium oxide, yttrium oxide, gallium nitride, aluminum nitride, silicon carbide, and/or silicon oxide.